

Byoung-Gon Yu

List of Publications by Year in descending order

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20
papers

462
citations

933447

10
h-index

940533

16
g-index

20
all docs

20
docs citations

20
times ranked

638
citing authors

#	ARTICLE	IF	CITATIONS
1	Direct formation of random wrinkle on emission surface for improved light out coupling and stable angular spectrum of white organic light emitting diodes. Journal of Luminescence, 2019, 205, 66-71.	3.1	4
2	Organic wrinkles embedded in high-index medium as planar internal scattering structures for organic light-emitting diodes. Organic Electronics, 2017, 46, 139-144.	2.6	25
3	Highly efficient green, blue, and white phosphorescent inverted organic light-emitting diodes by improving charge injection and balance. Journal of Materials Chemistry C, 2017, 5, 9911-9919.	5.5	10
4	Flexion bonding transfer of multilayered graphene as a top electrode in transparent organic light-emitting diodes. Scientific Reports, 2015, 5, 17748.	3.3	35
5	46.2: A Novel Laminated Organic Light-Emitting Diodes with a Multi-Layered Graphene Top Anode. Digest of Technical Papers SID International Symposium, 2015, 46, 688-691.	0.3	1
6	Paper No S4.4: Colored OLED With a Multilayered Graphene Electrode for Light-Adaptable Displays. Digest of Technical Papers SID International Symposium, 2015, 46, 20-20.	0.3	0
7	Organic wrinkles for energy efficient organic light emitting diodes. Organic Electronics, 2015, 26, 273-278.	2.6	45
8	Polymeric ferroelectric and oxide semiconductor-based fully transparent memristor cell. Applied Physics A: Materials Science and Processing, 2011, 102, 983-990.	2.3	11
9	Low temperature grown polycrystalline La _{0.7} Sr _{0.3} MnO ₃ thin films on amorphous SiO ₂ substrates by rf magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 595-600.	2.1	3
10	Phase-Change-Driven Programmable Switch for Nonvolatile Logic Applications. IEEE Electron Device Letters, 2009, 30, 371-373.	3.9	16
11	PROPERTIES OF FERROELECTRIC P(VDF-TrFE) 70/30 COPOLYMER FILMS AS A GATE DIELECTRIC. Integrated Ferroelectrics, 2008, 100, 198-205.	0.7	22
12	Novel Process for the Electrodes of Microbolometer. , 2007, , .		1
13	Sb-Se-based phase-change memory device with lower power and higher speed operations. IEEE Electron Device Letters, 2006, 27, 445-447.	3.9	103
14	Characterization of silver-saturated GeTe chalcogenide thin films for nonvolatile random access memory. Journal of Vacuum Science & Technology B, 2006, 24, 721.	1.3	35
15	Polycrystalline silicon-germanium heating layer for phase-change memory applications. Applied Physics Letters, 2006, 89, 053517.	3.3	50
16	Fabrication of Ferroelectric Gate Memory Device Using BLT/HfO ₂ /Si Gate Structure. Integrated Ferroelectrics, 2003, 52, 195-203.	0.7	1
17	Electrical Properties of SrTa ₂ O ₆ Thin Films Deposited by Plasma Enhanced Atomic Layer Deposition (Peald). Materials Research Society Symposia Proceedings, 2001, 685, 1.	0.1	0
18	Fabrication and characterization of MFISFET using Al ₂ O ₃ insulating layer for non-volatile memory. Integrated Ferroelectrics, 2001, 34, 113-120.	0.7	5

#	ARTICLE	IF	CITATIONS
19	Dielectric and ferroelectric response as a function of annealing temperature and film thickness of sol-gel deposited Pb(Zr _{0.52} Ti _{0.48})O ₃ thin film. Journal of Applied Physics, 1999, 86, 2700-2711.	2.5	94
20	Polycrystalline Silicon Field Emitter Arrays With A Gated Structure. , 1997, , .		1